

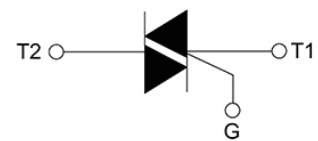
DESCRIPTION:

The chip triac is suitable for general purpose AC switching. It can be used as an ON/OFF function in applications such as heating regulation, induction motor starting circuits, for phase control operation in light dimmers, motor speed controllers.



MAIN FEATURES

Symbol	Value	Unit
$I_{T(RMS)}$	16	A
V_{DRM}/V_{RRM}	600	V
$I_{GT\ I / II / III / IV}$	25/25/25/50	mA



ABSOLUTE MAXIMUM RATINGS

Parameter		Symbol	Value	Unit
Storage junction temperature range		T _{stg}	-40-150	℃
Operating junction temperature range		T _j	-40-125	℃
Repetitive peak off-state voltage (T _j =25℃)		V _{DRM}	600	V
Repetitive peak reverse voltage (T _j =25℃)		V _{RRM}	600	V
RMS on-state current (T _c ≤100℃)		I _{T(RMS)}	16	A
Non repetitive surge peak on-state current (full cycle , t _p =20ms , T _j =25℃)		I _{TSM}	160	A
Non repetitive surge peak on-state current (full cycle , t _p =16.6ms , T _j =25℃)			176	
I ² t value for fusing (t _p =10ms , T _j =25℃)		I ² t	128	A ² s
Critical rate of rise of on-state current (I _G =2×I _{GT} , f=100Hz , T _j =125℃)	I - II	di/dt	80	A/μs
	III-IV		40	
Peak gate current (t _p =20μs , T _j =125℃)		I _{GM}	4	A
Average gate power dissipation (T _j =125℃)		P _{G(AV)}	0.5	W
Peak gate power		P _{GM}	10	W
Peak pulse voltage (T _j =25℃; non-repetitive,off-state;FIG)		V _{pp}	3.5	kV

ELECTRICAL CHARACTERISTICS ($T_j=25^{\circ}\text{C}$ unless otherwise specified)

Symbol	Test Condition	Quadrant	Value		Unit
I_{GT}	$V_D=12\text{V } R_L=33\Omega$	I - II - III	MAX.	25	mA
		IV		50	
V_{GT}		ALL	MAX.	1	V
V_{GD}	$V_D=V_{DRM} T_j=125^{\circ}\text{C}$ $R_L=3.3\text{k}\Omega$	ALL	MIN.	0.2	V
I_L	$I_G=1.2I_{GT}$	I - III - IV	MAX.	40	mA
		II		80	
I_H	$I_T=500\text{mA}$		MAX.	40	mA
dV/dt	$V_D=400\text{V}$ Gate Open $T_j=125^{\circ}\text{C}$		MIN.	800	V/ μs
$(dV/dt)_c$	$(dI/dt)_c=7\text{A/ms}$, $T_j=125^{\circ}\text{C}$		MIN.	6	V/ μs
t_{on}	$I_G=80\text{mA } I_A=400\text{mA } I_R=40\text{mA}$		TYP.	10	μs
t_{off}	$T_j=25^{\circ}\text{C}$			70	

STATIC CHARACTERISTICS

Symbol	Parameter		Value(MAX.)	Unit
V_{TM}	$I_{TM}=22.5\text{A } t_p=380\mu\text{s}$	$T_j=25^{\circ}\text{C}$	1.5	V
V_{TO}	Threshold voltage	$T_j=125^{\circ}\text{C}$	0.77	V
R_D	Dynamic resistance	$T_j=125^{\circ}\text{C}$	30	$\text{m}\Omega$
I_{DRM}	$V_D=V_{DRM} V_R=V_{RRM}$	$T_j=25^{\circ}\text{C}$	5	μA
I_{RRM}		$T_j=125^{\circ}\text{C}$	0.4	mA

THERMAL RESISTANCES

Symbol	Parameter	Value	Unit
$R_{th(j-c)}$	junction to case (AC)	1.1	$^{\circ}\text{C/W}$
$R_{th(j-a)}$	junction to ambient (AC)	60	$^{\circ}\text{C/W}$

FIG : Maximum power dissipation versus RMS on-state current

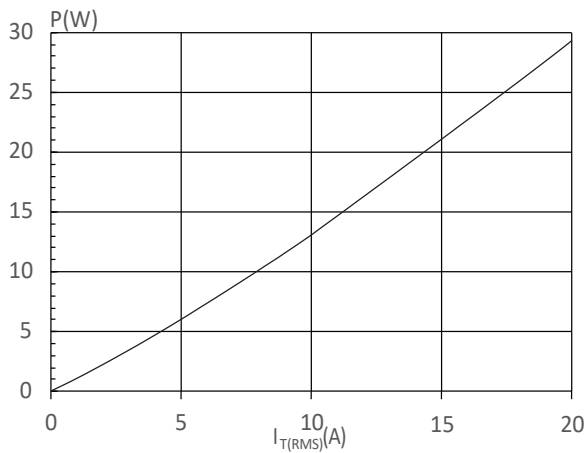


FIG : Surge peak on-state current versus number of cycles

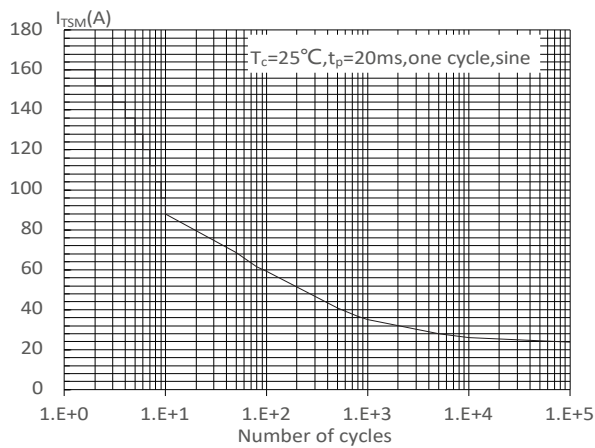


FIG : Non-repetitive surge peak on-state current for a sinusoidal pulse with width $t_p < 20ms$, and corresponding value of I^2t (I - II : $di/dt < 80A/\mu s$; III-IV : $di/dt < 40A/\mu s$)

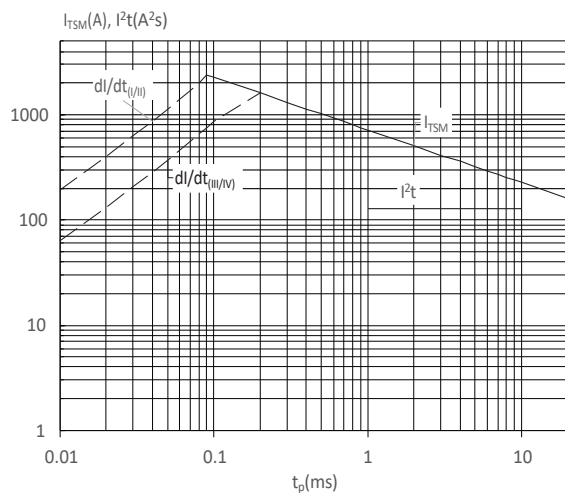


FIG : RMS on-state current versus case temperature

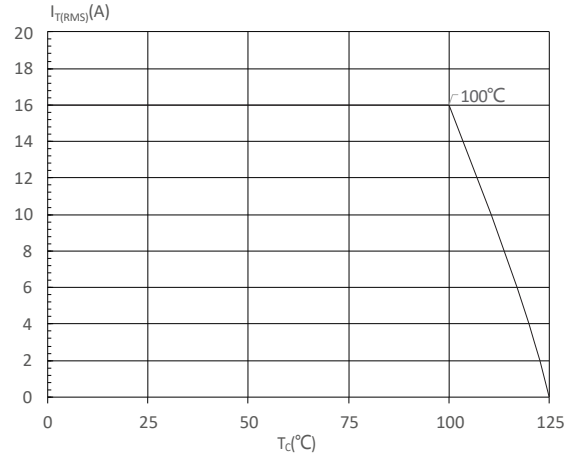


FIG : On-state characteristics

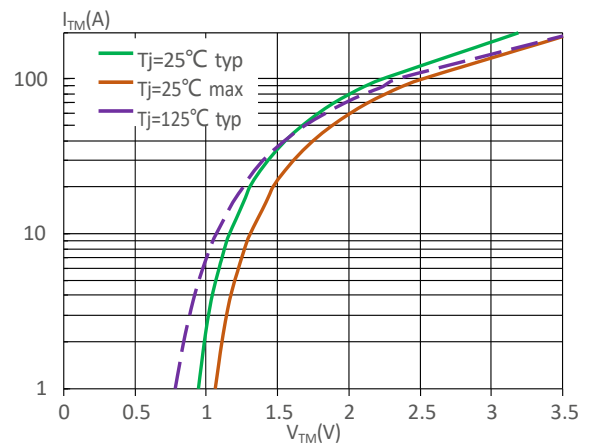


FIG : Relative variations of gate trigger current, holding current and latching current versus junction temperature

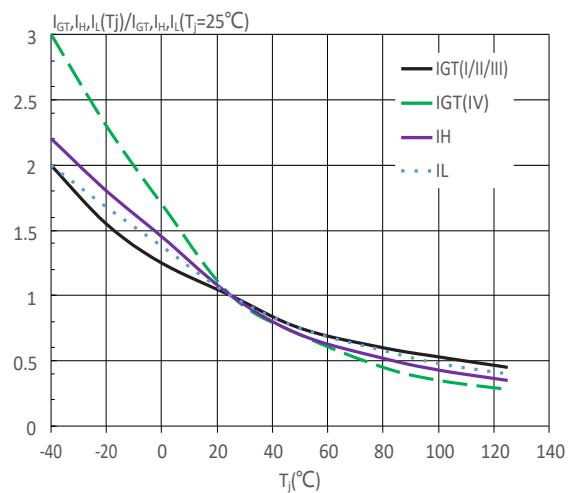
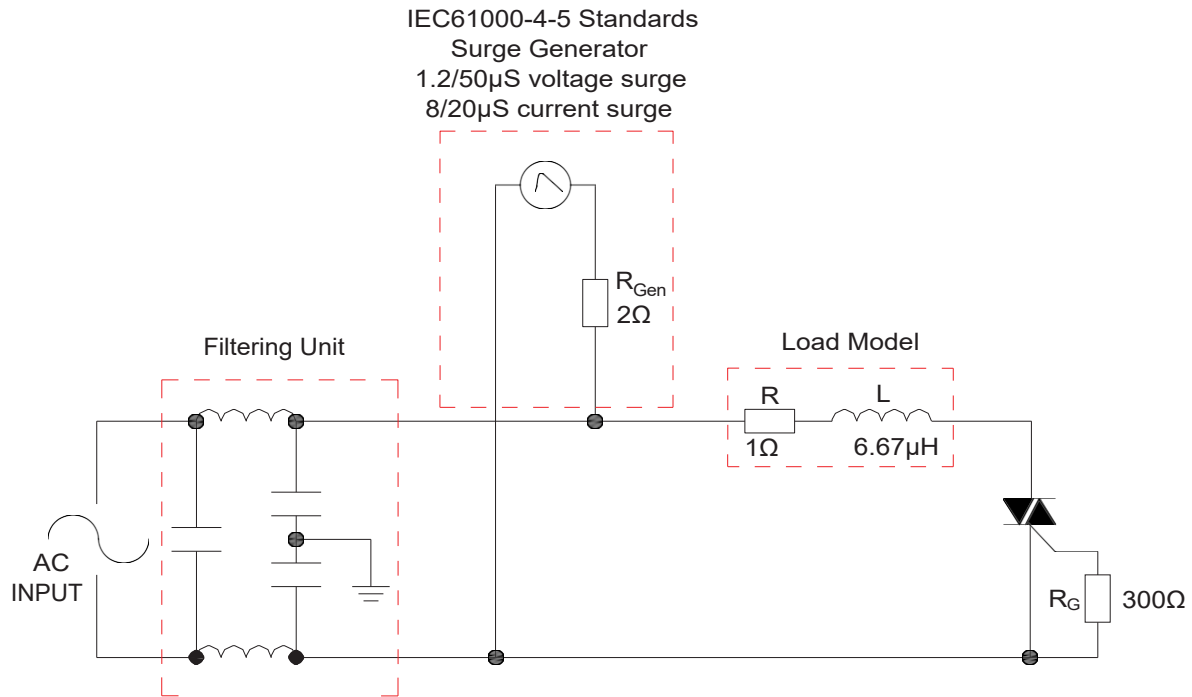


FIG : Test circuit for inductive and resistive loads to IEC-61000-4-5 standards



LEAD FORMING AND SOLDERING

Refer to the application note “Assembly Instructions for Thyristors in Through-hole Package” released by JieJie Microelectronics